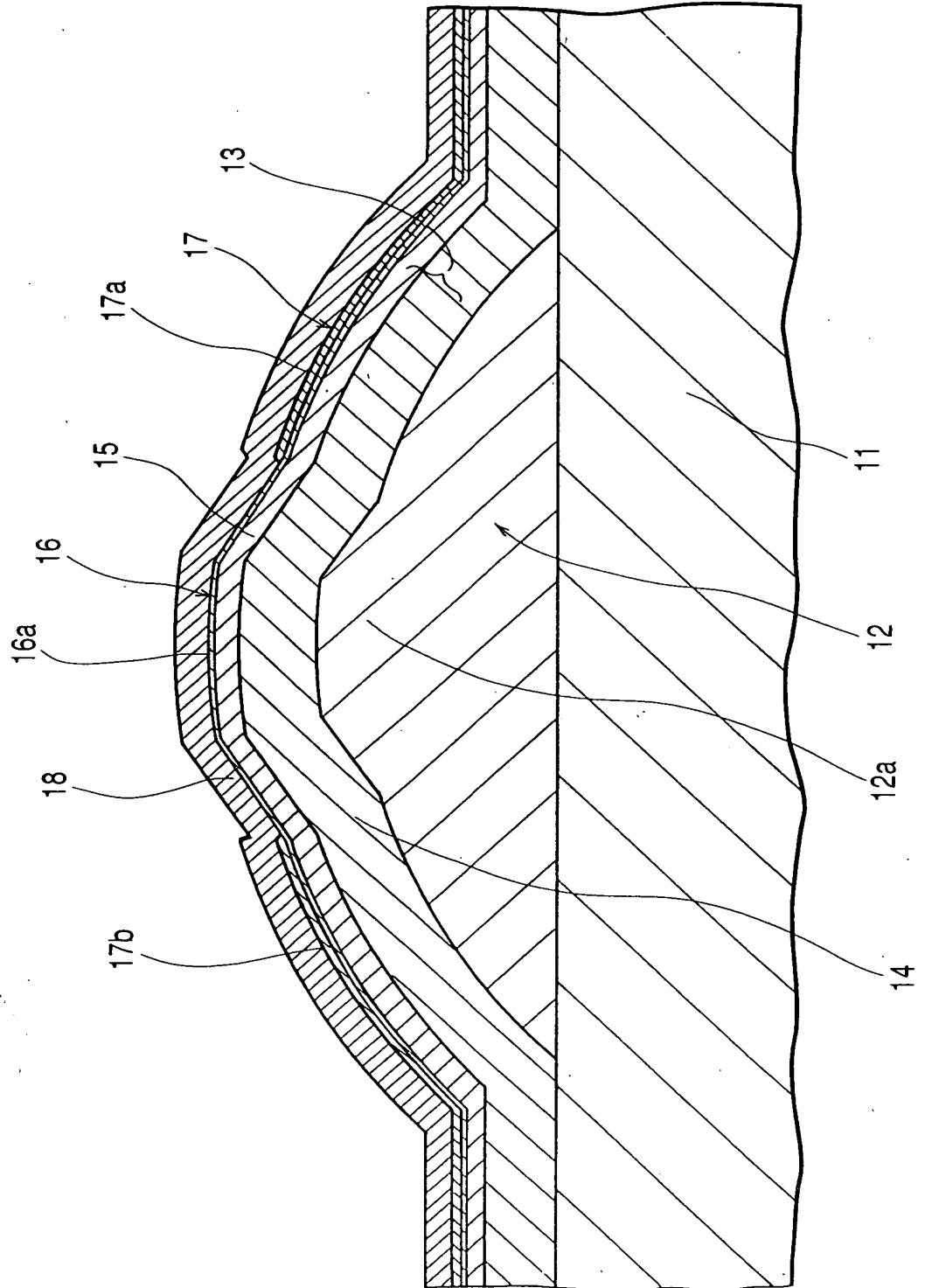


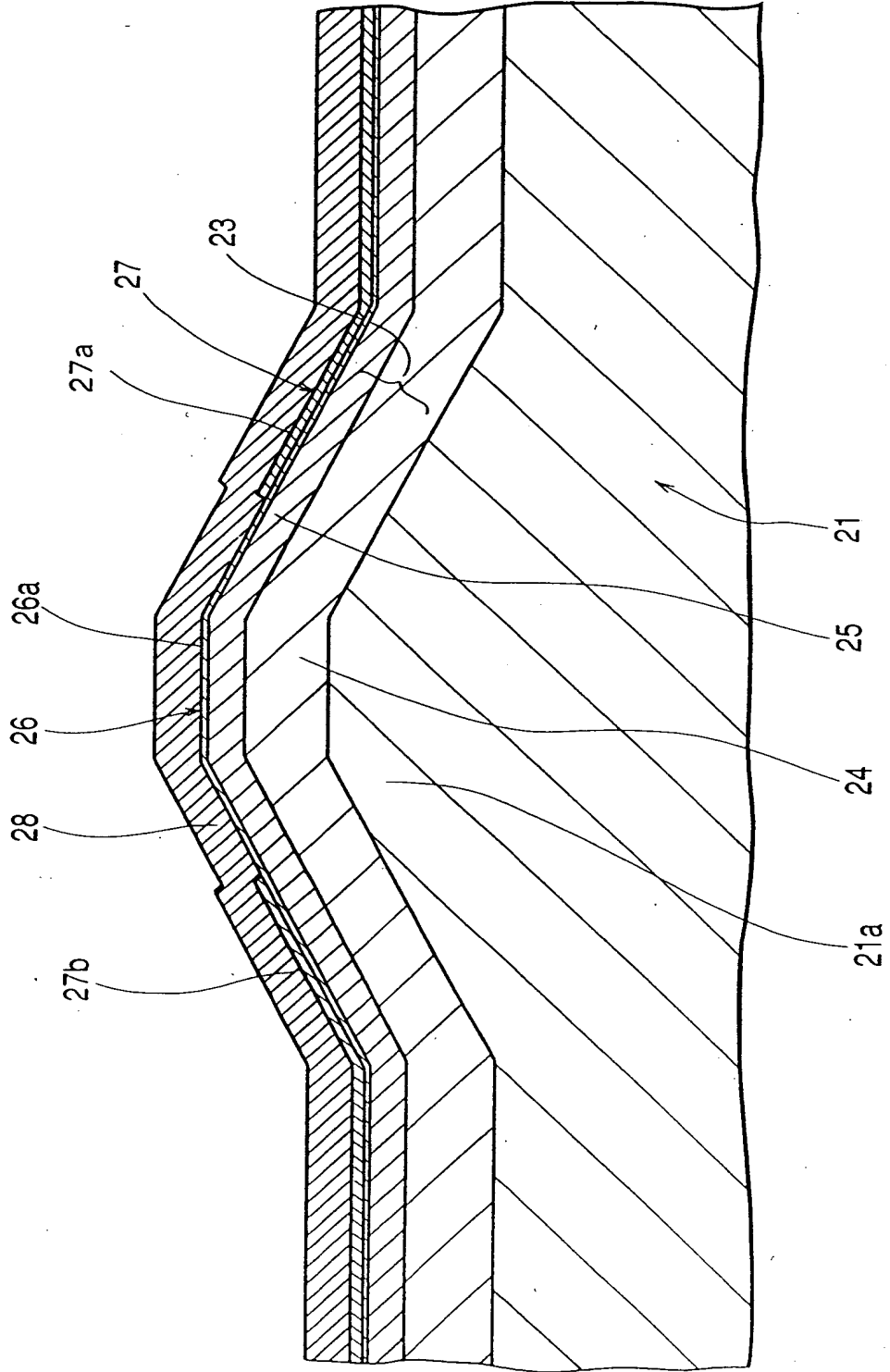
1 / 7

FIG. 1



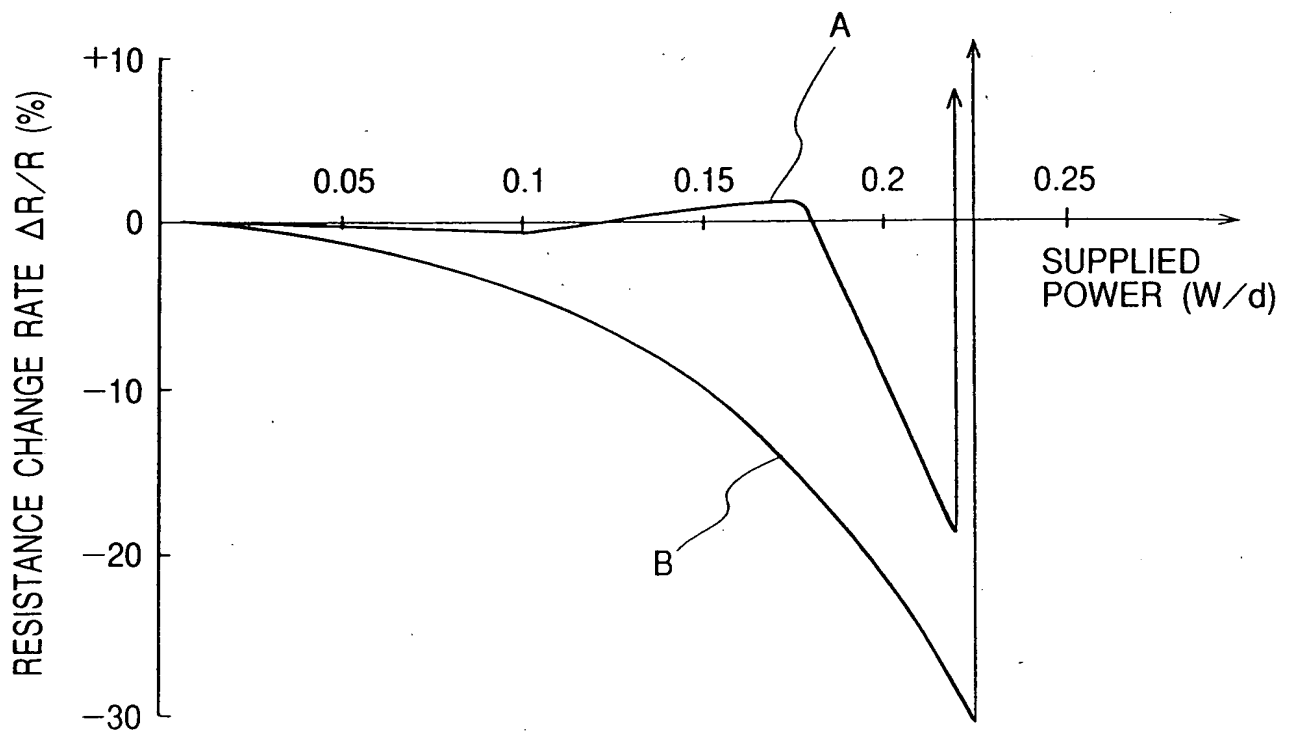
2 / 7

FIG. 2

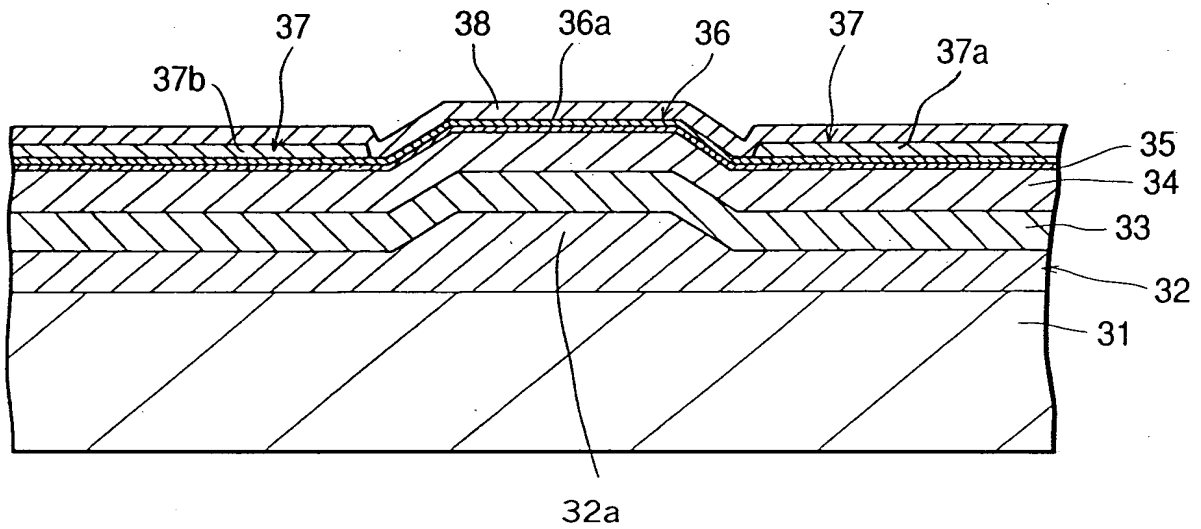


3/7

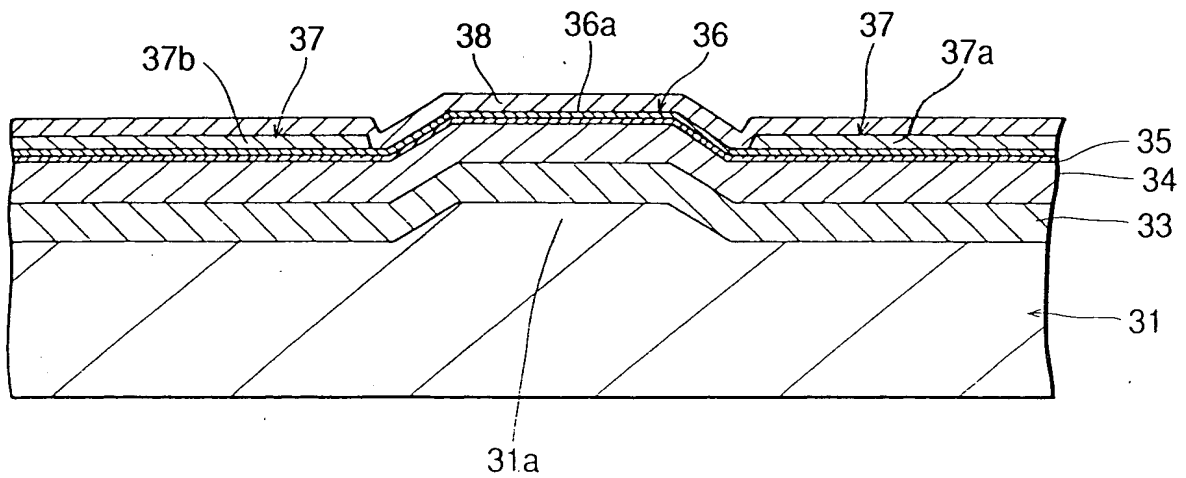
FIG. 3



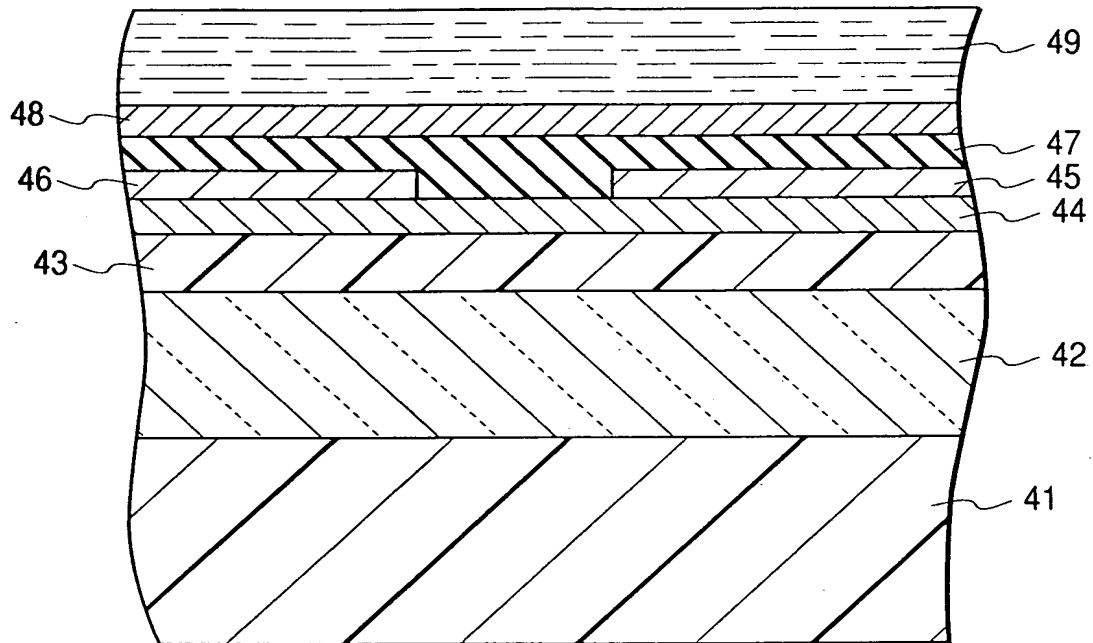
**FIG. 4**



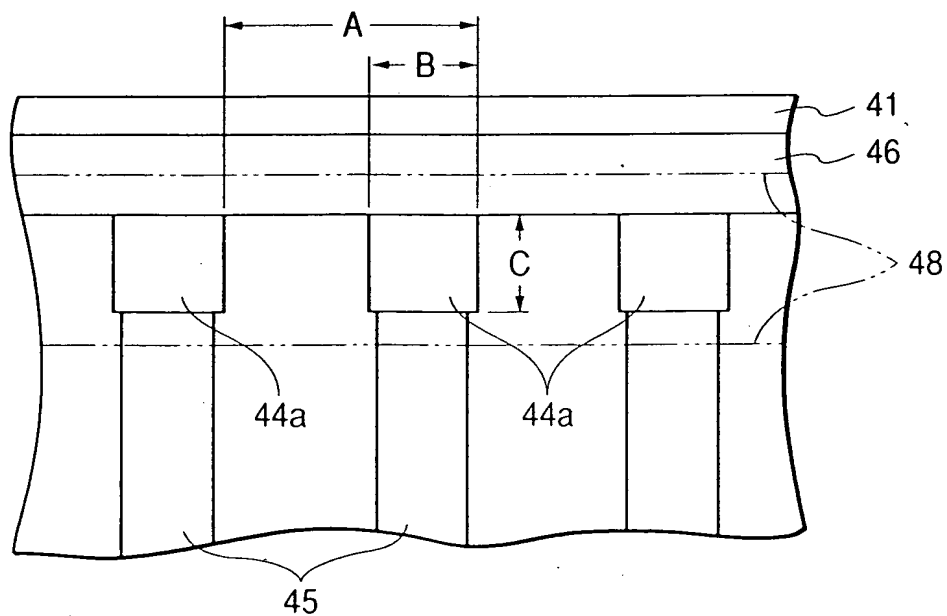
**FIG. 5**



**FIG. 6**

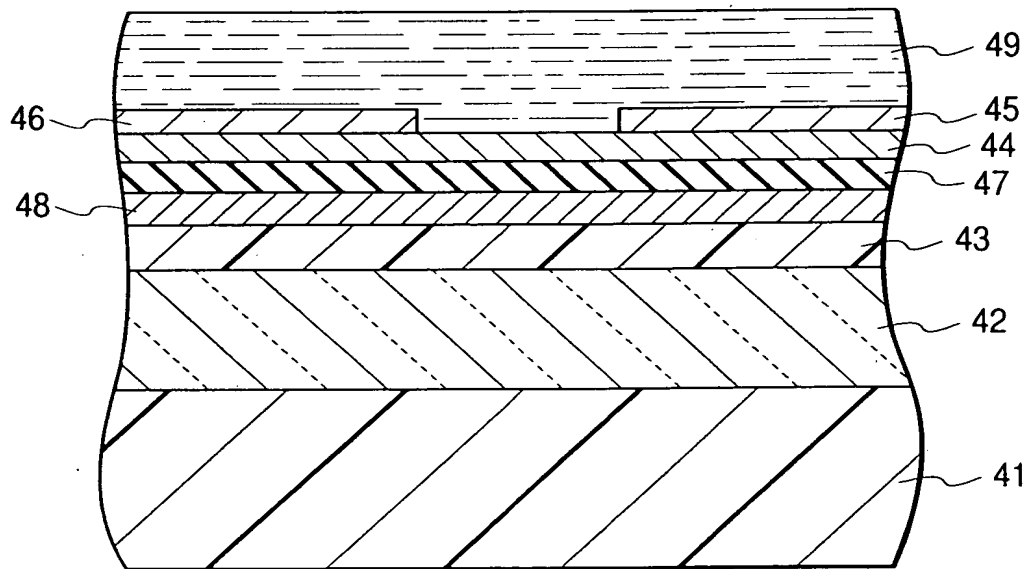


**FIG. 7**



6 / 7

FIG. 8



This diagram shows a cross-sectional view of a semiconductor device. A substrate 101 is shown with a series of parallel diagonal hatching lines. A trench 102 is formed in the substrate, with its side walls labeled 102a. The bottom of the trench is labeled 103. A layer 104 is deposited on the bottom and side walls of the trench. This layer is divided into two regions: 104a, which is the upper portion of the layer, and 104b, which is the lower portion. A layer 105 is deposited on top of the trench structure. The top surface of the layer 105 is labeled 103a. The top surface of the layer 104 is labeled 103.